



40V COMPLEMENTARY NPN-PNP SMALL SIGNAL TRANSISTOR IN DFN1310-6

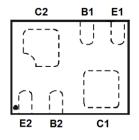
Features

- Complementary Pair One 3904-Type NPN
 One 3906-Type PNP
- Ultra-Small Surface Mount Package
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: X2-DFN1310-6 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @4)
- Weight: 0.006 grams (Approximate)





E1, B1, C1 = PNP 3906 E2, B2, C2 = NPN 3904

Pinout Top View

Ordering Information (Note 4)

ĺ	Product	Standard	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
	MMDT3946FL3-7	AEC-Q101	47	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

47

47 = Product Type Marking Code



Absolute Maximum Ratings, NPN 3904 (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	200	mA

Absolute Maximum Ratings, PNP 3906 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	$V_{\sf CEO}$	-40	V
Emitter-Base Voltage	V_{EBO}	-6.0	V
Collector Current	Ic	-200	mA

Thermal Characteristics, Total Device (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_{D}	370	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{ hetaJA}$	339	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

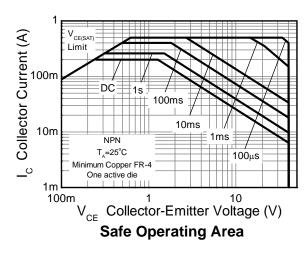
ESD Ratings (Note 6)

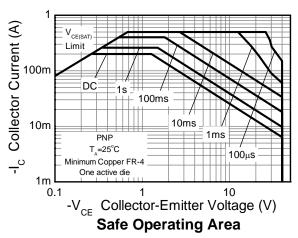
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

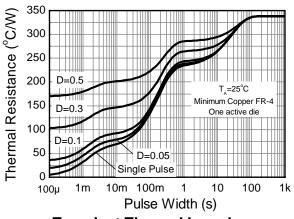
Notes: 5. For a device mounted on minimum recommended pad layout that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

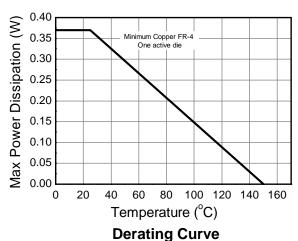


Thermal Characteristics and Derating Information

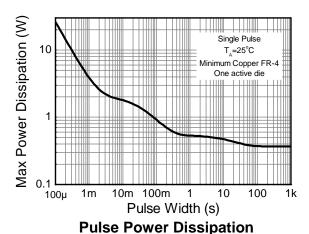








Transient Thermal Impedance



MMDT3946FL3

Datasheet Number DS38537 Rev.1 - 2



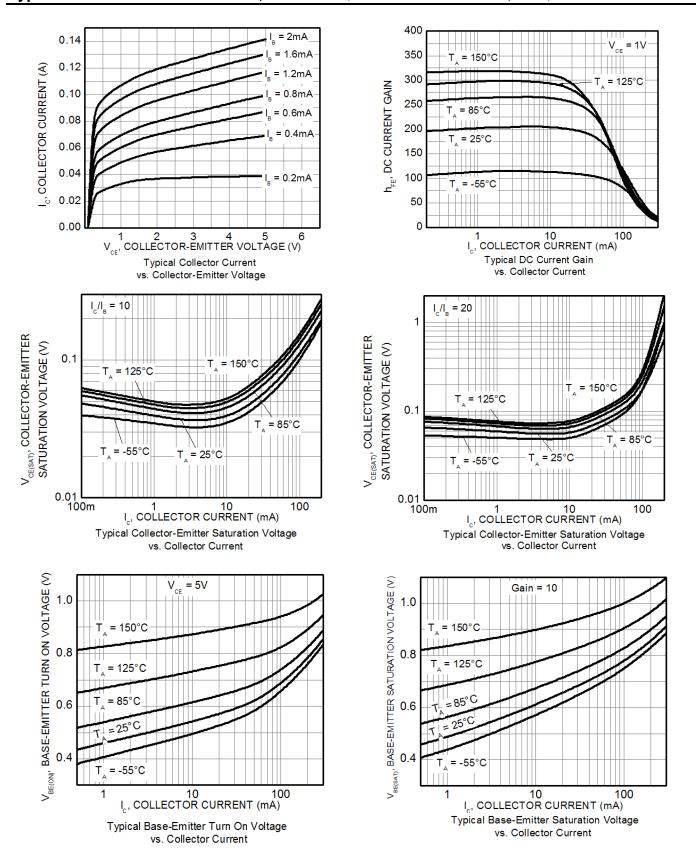
Electrical Characteristics, NPN 3904 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Collector-Base Breakdown Voltage	BV _{CBO}	60			V	$I_C = 100 \mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	BV _{CEO}	40	_	_	V	$I_C = 1.0 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0	_	_	V	$I_E = 100 \mu A, I_C = 0$	
Collector Cutoff Current	I _{CEX}	_	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$	
Base Cutoff Current	I _{BL}	_	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$	
ON CHARACTERISTICS (Note 7)							
Static Forward Current Transfer Ratio	h _{FE}	40 70 100 60 30		 300 	_	$\begin{split} I_C &= 100 \mu A, \ V_{CE} = \ 1.0 V \\ I_C &= 1.0 m A, \ V_{CE} = \ 1.0 V \\ I_C &= 10 m A, \ V_{CE} = \ 1.0 V \\ I_C &= 50 m A, \ V_{CE} = \ 1.0 V \\ I_C &= 100 m A, \ V_{CE} = \ 1.0 V \end{split}$	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	_	0.20 0.30	V	$I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 50$ mA, $I_B = 5.0$ mA	
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65	_	0.85 0.95	V	$I_C = 10mA, I_B = 1.0mA$ $I_C = 50mA, I_B = 5.0mA$	
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C _{obo}	_		4.0	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$	
Input Capacitance	C _{ibo}	_		9.5	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_{C} = 0$	
Current Gain-Bandwidth Product	f⊤		300		MHz	$V_{CE} = 20V$, $I_C = 20mA$, $f = 100MHz$	
SWITCHING CHARACTERISTICS	SWITCHING CHARACTERISTICS						
Delay Time	t _D	_		35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$	
Rise Time	t _R	_		35	35 ns $V_{BE} = 0.5V$, $I_{B1} = 1.0$ mA		
Storage Time	t _S	_		200	ns	V _{CC} = 3.0V, I _C = 10mA,	
Fall Time	t _F	_		50	ns	$I_{B1} = 1.0 \text{mA}, I_{B2} = -1.0 \text{mA}$	

Note: 7. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics, NPN 3904 (@T_A = +25°C, unless otherwise specified.)





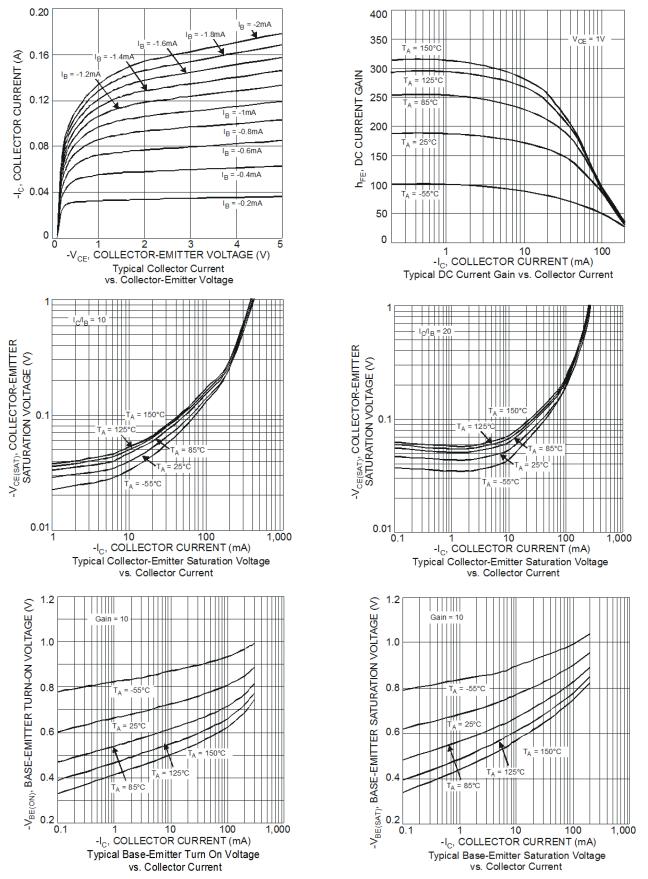
Electrical Characteristics, PNP 3906 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Collector-Base Breakdown Voltage	BV _{CBO}	-40		_	٧	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	-40		_	V	$I_C = -1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-6.0	_	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CEX}	_	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$
Base Cutoff Current	I _{BL}	_	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$
ON CHARACTERISTICS (Note 7)						
Static Forward Current Transfer Ratio	h _{FE}	60 80 100 60 30		300 — —		$\begin{split} I_C &= -100 \mu A, \ V_{CE} = \ -1.0 V \\ I_C &= -1.0 m A, \ V_{CE} = \ -1.0 V \\ I_C &= -10 m A, \ V_{CE} = \ -1.0 V \\ I_C &= -50 m A, \ V_{CE} = \ -1.0 V \\ I_C &= -100 m A, \ V_{CE} = \ -1.0 V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_		-0.25 -0.40	>	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	-0.65 —		-0.85 -0.95	٧	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	_		4.5	pF	$V_{CB} = -5.0V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C _{ibo}	_	_	10	pF	$V_{EB} = -0.5V$, $f = 1.0MHz$, $I_C = 0$
Current Gain-Bandwidth Product	f⊤	_	300	_	MHz	$V_{CE} = -20V, I_{C} = -10mA,$ f = 100MHz
SWITCHING CHARACTERISTICS						
Delay Time	t _D	_	_	35	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Rise Time	t _R	_		35	ns	$V_{BE} = -0.5V, I_{B1} = -1.0mA$
Storage Time	ts	_	_	225	ns	V _{CC} = -3.0V, I _C = -10mA,
Fall Time	t _F	_		75	ns	$I_{B1} = -1.0 \text{mA}, I_{B2} = 1.0 \text{mA}$

Note: 7. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics, PNP 3906 (@TA = +25°C, unless otherwise specified.)

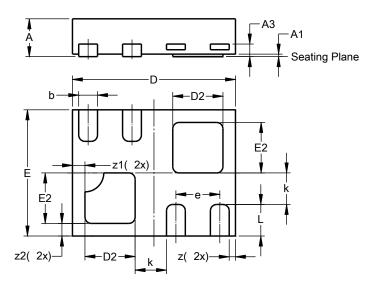




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1310-6 (Type B)

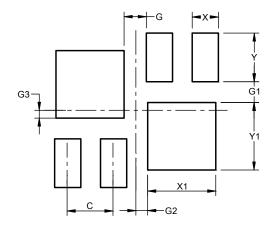


X2-DFN1310-6 (Type B)							
Dim	Min	Max	Тур				
Α	0.25	0.35	0.30				
A1	0	0.05	0.02				
A3			0.100				
b	0.10	0.20	0.15				
D	1.25	1.35	1.30				
D2	0.30	0.50	0.40				
Е	0.95	1.05	1.00				
E2	0.30	0.50	0.40				
е	-		0.35				
k	0.15						
L	L 0.20		0.25				
Z			0.05				
z1			0.10				
z2			0.10				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1310-6 (Type B)



Dimensions	Value (in mm)			
С	0.350			
G	0.17			
G1	0.16			
G2	0.09			
G3	0.06			
Х	0.20			
X1	0.52			
Υ	0.375			
Y1	0.52			



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